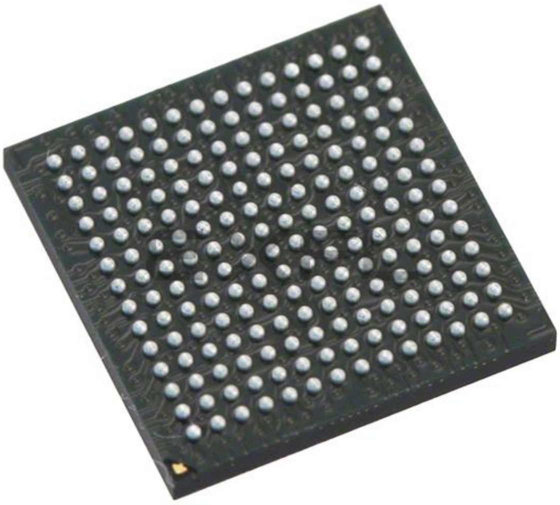
AMD Xilinx - XC6SLX9-L1CPG196I Datasheet



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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	715
Number of Logic Elements/Cells	9152
Total RAM Bits	589824
Number of I/O	106
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	196-TFBGA, CSBGA
Supplier Device Package	196-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6slx9-l1cpg196i

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Table 2: **Recommended Operating Conditions**(1)

Symbol	Description			Min	Typ	Max	Units
V_{CCINT}	Internal supply voltage relative to GND	-3, -3N, -2	Standard performance(2)	1.14	1.2	1.26	V
		-3, -2	Extended performance(2)	1.2	1.23	1.26	V
		-1L	Standard performance(2)	0.95	1.0	1.05	V
V_{CCAUX}(3)(4)	Auxiliary supply voltage relative to GND	V_{CCAUX} = 2.5V(5)		2.375	2.5	2.625	V
		V_{CCAUX} = 3.3V		3.15	3.3	3.45	V
V_{CCO}(6)(7)(8)	Output supply voltage relative to GND			1.1	–	3.45	V
V_{IN}	Input voltage relative to GND	All I/O standards (except PCI)	Commercial temperature (C)	–0.5	–	4.0	V
			Industrial temperature (I)	–0.5	–	3.95	V
			Expanded (Q) temperature	–0.5	–	3.95	V
		PCI I/O standard(9)		–0.5	–	V_{CCO} + 0.5	V
I_{IN}(10)	Maximum current through pin using PCI I/O standard when forward biasing the clamp diode.(9)		Commercial (C) and Industrial temperature (I)	–	–	10	mA
			Expanded (Q) temperature	–	–	7	mA
V_{BATT}(11)	Battery voltage relative to GND, T_j = 0°C to +85°C (LX75, LX75T, LX100, LX100T, LX150, and LX150T only)			1.0	–	3.6	V
T_j	Junction temperature operating range	Commercial (C) range		0	–	85	°C
		Industrial temperature (I) range		–40	–	100	°C
		Expanded (Q) temperature range		–40	–	125	°C

Notes:

1. All voltages are relative to ground.
2. See *Interface Performances for Memory Interfaces* in Table 25. The extended performance range is specified for designs not using the standard V_{CCINT} voltage range. The standard V_{CCINT} voltage range is used for:
    - Designs that do not use an MCB
    - LX4 devices
    - Devices in the TQG144 or CPG196 packages
    - Devices with the -3N speed grade
3. Recommended maximum voltage droop for V_{CCAUX} is 10 mV/ms.
4. During configuration, if V_{CCO_2} is 1.8V, then V_{CCAUX} must be 2.5V.
5. The -1L devices require V_{CCAUX} = 2.5V when using the LVDS_25, LVDS_33, BLVDS_25, LVPECL_25, RSDS_25, RSDS_33, PPDS_25, and PPDS_33 I/O standards on inputs. LVPECL_33 is not supported in the -1L devices.
6. Configuration data is retained even if V_{CCO} drops to 0V.
7. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
8. For PCI systems, the transmitter and receiver should have common supplies for V_{CCO}.
9. Devices with a -1L speed grade do not support Xilinx PCI IP.
10. Do not exceed a total of 100 mA per bank.
11. V_{BATT} is required to maintain the battery backed RAM (BBR) AES key when V_{CCAUX} is not applied. Once V_{CCAUX} is applied, V_{BATT} can be unconnected. When BBR is not used, Xilinx recommends connecting to V_{CCAUX} or GND. However, V_{BATT} can be unconnected.

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description		Min	Typ	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)		0.8	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)		2.0	–	–	V
I_{REF}	V_{REF} leakage current per pin for commercial (C) and industrial (I) devices		–10	–	10	μA
	V_{REF} leakage current per pin for expanded (Q) devices		–15	–	15	μA
I_L	Input or output leakage current per pin (sample-tested) for commercial (C) and industrial (I) devices		–10	–	10	μA
	Input or output leakage current per pin (sample-tested) for expanded (Q) devices		–15	–	15	μA
I_{HS}	Leakage current on pins during hot socketing with FPGA unpowered	All pins except PROGRAM_B, DONE, and JTAG pins when HSWAPEN = 1	–20	–	20	μA
		PROGRAM_B, DONE, and JTAG pins, or other pins when HSWAPEN = 0	$I_{HS} + I_{RPU}$			μA
C_{IN}(1)	Die input capacitance at the pad		–	–	10	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V or V_{CCAUX} = 3.3V		200	–	500	μA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V or V_{CCAUX} = 2.5V		120	–	350	μA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V		60	–	200	μA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V		40	–	150	μA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V		12	–	100	μA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = V_{CCO}, V_{CCAUX} = 3.3V		200	–	550	μA
	Pad pull-down (when selected) @ V_{IN} = V_{CCO}, V_{CCAUX} = 2.5V		140	–	400	μA
I_{BATT}(2)	Battery supply current		–	–	150	nA
R_{DT}(3)	Resistance of optional input differential termination circuit, V_{CCAUX} = 3.3V		–	100	–	Ω
R_{IN_TERM}(5)	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for commercial (C) and industrial (I) devices		23	25	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for expanded (Q) devices		20	25	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for commercial (C) and industrial (I) devices		39	50	72	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for expanded (Q) devices		32	50	74	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for commercial (C) and industrial (I) devices		56	75	109	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for expanded (Q) devices		47	75	115	Ω
R_{OUT_TERM}	Thevenin equivalent resistance of programmable output termination (UNTUNED_25)		11	25	52	Ω
	Thevenin equivalent resistance of programmable output termination (UNTUNED_50)		21	50	96	Ω
	Thevenin equivalent resistance of programmable output termination (UNTUNED_75)		29	75	145	Ω

Notes:

1. The C_{IN} measurement represents the die capacitance at the pad, not including the package.
2. Maximum value specified for worst case process at 25°C. LX75, LX75T, LX100, LX100T, LX150, and LX150T only.
3. Refer to IBIS models for R_{DT} variation and for values at V_{CCAUX} = 2.5V. IBIS values for R_{DT} are valid for all temperature ranges.
4. V_{CCO2} is not required for data retention. The minimum V_{CCO2} for power-on reset and configuration is 1.65V.
5. Termination resistance to a V_{CCO}/2 level.

SelectIO™ Interface DC Input and Output Levels

Table 7: **Recommended Operating Conditions for User I/Os Using Single-Ended Standards**

I/O Standard	V_{CCO} for Drivers(1)			V_{REF} for Inputs		
	V, Min	V, Nom	V, Max	V, Min	V, Nom	V, Max
LVTTL	3.0	3.3	3.45	V_{REF} is not used for these I/O standards		
LVCMOS33	3.0	3.3	3.45			
LVCMOS25	2.3	2.5	2.7			
LVCMOS18	1.65	1.8	1.95			
LVCMOS18_JEDEC	1.65	1.8	1.95			
LVCMOS15	1.4	1.5	1.6			
LVCMOS15_JEDEC	1.4	1.5	1.6			
LVCMOS12	1.1	1.2	1.3			
LVCMOS12_JEDEC	1.1	1.2	1.3			
PCI33_3(2)	3.0	3.3	3.45			
PCI66_3(2)	3.0	3.3	3.45			
I2C	2.7	3.0	3.45			
SMBUS	2.7	3.0	3.45			
SDIO	3.0	3.3	3.45			
MOBILE_DDR	1.7	1.8	1.9			
HSTL_I	1.4	1.5	1.6	0.68	0.75	0.9
HSTL_II	1.4	1.5	1.6	0.68	0.75	0.9
HSTL_III	1.4	1.5	1.6	–	0.9	–
HSTL_I_18	1.7	1.8	1.9	0.8	0.9	1.1
HSTL_II_18	1.7	1.8	1.9	–	0.9	–
HSTL_III_18	1.7	1.8	1.9	–	1.1	–
SSTL3_I	3.0	3.3	3.45	1.3	1.5	1.7
SSTL3_II	3.0	3.3	3.45	1.3	1.5	1.7
SSTL2_I	2.3	2.5	2.7	1.13	1.25	1.38
SSTL2_II	2.3	2.5	2.7	1.13	1.25	1.38
SSTL18_I	1.7	1.8	1.9	0.833	0.9	0.969
SSTL18_II	1.7	1.8	1.9	0.833	0.9	0.969
SSTL15_II	1.425	1.5	1.575	0.69	0.75	0.81

Notes:

1. V_{CCO} range required when using I/O standard for an output. Also required for MOBILE_DDR, PCI33_3, LVCMOS18_JEDEC, LVCMOS15_JEDEC, and LVCMOS12_JEDEC inputs, and for LVCMOS25 inputs when V_{CCAUX} = 3.3V.
2. For PCI systems, the transmitter and receiver should have common supplies for V_{CCO}.

In Table 9 and Table 10, values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: **Single-Ended I/O Standard DC Input and Output Levels**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVTTL	–0.5	0.8	2.0	4.1	0.4	2.4	Note 2	Note 2
LVCMOS33	–0.5	0.8	2.0	4.1	0.4	$V_{CCO} - 0.4$	Note 2	Note 2
LVCMOS25	–0.5	0.7	1.7	4.1	0.4	$V_{CCO} - 0.4$	Note 2	Note 2
LVCMOS18	–0.5	0.38	0.8	4.1	0.45	$V_{CCO} - 0.45$	Note 2	Note 2
LVCMOS18 (-1L)	–0.5	0.33	0.71	4.1	0.45	$V_{CCO} - 0.45$	Note 2	Note 2
LVCMOS18_JEDEC	–0.5	35% V_{CCO}	65% V_{CCO}	4.1	0.45	$V_{CCO} - 0.45$	Note 2	Note 2
LVCMOS15	–0.5	0.38	0.8	4.1	25% V_{CCO}	75% V_{CCO}	Note 3	Note 3
LVCMOS15 (-1L)	–0.5	0.33	0.71	4.1	25% V_{CCO}	75% V_{CCO}	Note 3	Note 3
LVCMOS15_JEDEC	–0.5	35% V_{CCO}	65% V_{CCO}	4.1	25% V_{CCO}	75% V_{CCO}	Note 3	Note 3
LVCMOS12	–0.5	0.38	0.8	4.1	0.4	$V_{CCO} - 0.4$	Note 4	Note 4
LVCMOS12 (-1L)	–0.5	0.33	0.71	4.1	0.4	$V_{CCO} - 0.4$	Note 4	Note 4
LVCMOS12_JEDEC	–0.5	35% V_{CCO}	65% V_{CCO}	4.1	0.4	$V_{CCO} - 0.4$	Note 4	Note 4
PCI33_3	–0.5	30% V_{CCO}	50% V_{CCO}	$V_{CCO} + 0.5$	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
PCI66_3	–0.5	30% V_{CCO}	50% V_{CCO}	$V_{CCO} + 0.5$	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
I2C	–0.5	25% V_{CCO}	70% V_{CCO}	4.1	20% V_{CCO}	–	3	–
SMBUS	–0.5	0.8	2.1	4.1	0.4	–	4	–
SDIO	–0.5	12.5% V_{CCO}	75% V_{CCO}	4.1	12.5% V_{CCO}	75% V_{CCO}	0.1	–0.1
MOBILE_DDR	–0.5	20% V_{CCO}	80% V_{CCO}	4.1	10% V_{CCO}	90% V_{CCO}	0.1	–0.1
HSTL_I	–0.5	$V_{REF} - 0.1$	$V_{REF} + 0.1$	4.1	0.4	$V_{CCO} - 0.4$	8	–8
HSTL_II	–0.5	$V_{REF} - 0.1$	$V_{REF} + 0.1$	4.1	0.4	$V_{CCO} - 0.4$	16	–16
HSTL_III	–0.5	$V_{REF} - 0.1$	$V_{REF} + 0.1$	4.1	0.4	$V_{CCO} - 0.4$	24	–8
HSTL_I_18	–0.5	$V_{REF} - 0.1$	$V_{REF} + 0.1$	4.1	0.4	$V_{CCO} - 0.4$	11	–11
HSTL_II_18	–0.5	$V_{REF} - 0.1$	$V_{REF} + 0.1$	4.1	0.4	$V_{CCO} - 0.4$	22	–22
HSTL_III_18	–0.5	$V_{REF} - 0.1$	$V_{REF} + 0.1$	4.1	0.4	$V_{CCO} - 0.4$	30	–11
SSTL3_I	–0.5	$V_{REF} - 0.2$	$V_{REF} + 0.2$	4.1	$V_{TT} - 0.6$	$V_{TT} + 0.6$	8	–8
SSTL3_II	–0.5	$V_{REF} - 0.2$	$V_{REF} + 0.2$	4.1	$V_{TT} - 0.8$	$V_{TT} + 0.8$	16	–16
SSTL2_I	–0.5	$V_{REF} - 0.15$	$V_{REF} + 0.15$	4.1	$V_{TT} - 0.61$	$V_{TT} + 0.61$	8.1	–8.1
SSTL2_II	–0.5	$V_{REF} - 0.15$	$V_{REF} + 0.15$	4.1	$V_{TT} - 0.81$	$V_{TT} + 0.81$	16.2	–16.2
SSTL18_I	–0.5	$V_{REF} - 0.125$	$V_{REF} + 0.125$	4.1	$V_{TT} - 0.47$	$V_{TT} + 0.47$	6.7	–6.7
SSTL18_II	–0.5	$V_{REF} - 0.125$	$V_{REF} + 0.125$	4.1	$V_{TT} - 0.60$	$V_{TT} + 0.60$	13.4	–13.4
SSTL15_II	–0.5	$V_{REF} - 0.1$	$V_{REF} + 0.1$	4.1	$V_{TT} - 0.4$	$V_{TT} + 0.4$	13.4	–13.4

Notes:

1. Tested according to relevant specifications.
2. Using drive strengths of 2, 4, 6, 8, 12, 16, or 24 mA.
3. Using drive strengths of 2, 4, 6, 8, 12, or 16 mA.
4. Using drive strengths of 2, 4, 6, 8, or 12 mA.
5. For more information, refer to UG381: *Spartan-6 FPGA SelectIO Resources User Guide*.

Table 10: **Differential I/O Standard DC Input and Output Levels**

	V_{ID}		V_{ICM}		V_{OD}		V_{OCM}		V_{OH}	V_{OL}
I/O Standard	**mV, Min**	**mV, Max**	**V, Min**	**V, Max**	**mV, Min**	**mV, Max**	**V, Min**	**V, Max**	**V, Min**	**V, Max**
LVDS_33(2)(3)	100	600	0.3	2.35	247	454	1.125	1.375	–	–
LVDS_25(2)(3)	100	600	0.3	2.35	247	454	1.125	1.375	–	–
BLVDS_25(2)(3)	100	–	0.3	2.35	240	460	Typical 50% V_{CCO}		–	–
MINI_LVDS_33	200	600	0.3	1.95	300	600	1.0	1.4	–	–
MINI_LVDS_25	200	600	0.3	1.95	300	600	1.0	1.4	–	–
LVPECL_33(2)(3)	100	1000	0.3	2.8(1)	Inputs only					
LVPECL_25(2)(3)	100	1000	0.3	1.95	Inputs only					
RSDS_33(2)(3)	100	–	0.3	1.5	100	400	1.0	1.4	–	–
RSDS_25(2)(3)	100	–	0.3	1.5	100	400	1.0	1.4	–	–
TMDS_33	150	1200	2.7	3.23(1)	400	800	$V_{CCO} - 0.405$	$V_{CCO} - 0.190$	–	–
PPDS_33(2)(3)	100	400	0.2	2.3	100	400	0.5	1.4	–	–
PPDS_25(2)(3)	100	400	0.2	2.3	100	400	0.5	1.4	–	–
DISPLAY_PORT	190	1260	0.3	2.35	–	–	Typical 50% V_{CCO}		–	–
DIFF_MOBILE_DDR	100	–	0.78	1.02	–	–	–	–	90% V_{CCO}	10% V_{CCO}
DIFF_HSTL_I	100	–	0.68	0.9	–	–	–	–	$V_{CCO} - 0.4$	0.4
DIFF_HSTL_II	100	–	0.68	0.9	–	–	–	–	$V_{CCO} - 0.4$	0.4
DIFF_HSTL_III	100	–	0.68	0.9	–	–	–	–	$V_{CCO} - 0.4$	0.4
DIFF_HSTL_I_18	100	–	0.8	1.1	–	–	–	–	$V_{CCO} - 0.4$	0.4
DIFF_HSTL_II_18	100	–	0.8	1.1	–	–	–	–	$V_{CCO} - 0.4$	0.4
DIFF_HSTL_III_18	100	–	0.8	1.1	–	–	–	–	$V_{CCO} - 0.4$	0.4
DIFF_SSTL3_I	100	–	1.0	1.9	–	–	–	–	$V_{TT} + 0.6$	$V_{TT} - 0.6$
DIFF_SSTL3_II	100	–	1.0	1.9	–	–	–	–	$V_{TT} + 0.8$	$V_{TT} - 0.8$
DIFF_SSTL2_I	100	–	1.0	1.5	–	–	–	–	$V_{TT} + 0.61$	$V_{TT} - 0.61$
DIFF_SSTL2_II	100	–	1.0	1.5	–	–	–	–	$V_{TT} + 0.81$	$V_{TT} - 0.81$
DIFF_SSTL18_I	100	–	0.7	1.1	–	–	–	–	$V_{TT} + 0.47$	$V_{TT} - 0.47$
DIFF_SSTL18_II	100	–	0.7	1.1	–	–	–	–	$V_{TT} + 0.6$	$V_{TT} - 0.6$
DIFF_SSTL15_II	100	–	0.55	0.95	–	–	–	–	$V_{TT} + 0.4$	$V_{TT} - 0.4$

Notes:

1. LVPECL_33 and TMDS_33 maximum V_{ICM} is the lower of V (maximum) or $V_{CCAUX} - (V_{ID}/2)$
2. When V_{CCAUX} = 3.3V, the DCD can be higher than 5% for $V_{ICM} < 0.7V$ when using these I/O standards: LVDS_25, LVDS_33, BLVDS_25, LVPECL_25, LVPECL_33, RSDS_25, RSDS_33, PPDS_25, and PPDS_33.
3. The -1L devices require V_{CCAUX} = 2.5V when using the LVDS_25, LVDS_33, BLVDS_25, LVPECL_25, RSDS_25, RSDS_33, PPDS_25, and PPDS_33 I/O standards on inputs. LVPECL_33 is not supported in the -1L devices.

eFUSE Read Endurance

Table 11 lists the minimum guaranteed number of read cycle operations for Device DNA and for the AES eFUSE key. For more information, see UG380: *Spartan-6 FPGA Configuration User Guide*.

Table 11: **eFUSE Read Endurance**

Symbol	Description	Speed Grade				Units (Min)
		-3	-3N	-2	-1L	
DNA_CYCLES	Number of DNA_PORT READ operations or JTAG ISC_DNA read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles
AES_CYCLES	Number of JTAG FUSE_KEY or FUSE_CNTL read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles

GTP Transceiver Specifications

GTP transceivers are available in the Spartan-6 LXT devices. See DS160: *Spartan-6 Family Overview* for more information.

GTP Transceiver DC Characteristics

Table 12: **Absolute Maximum Ratings for GTP Transceivers(1)**

Symbol	Description	MIn	Max	Units
MGTAVCC	Analog supply voltage for the GTP transmitter and receiver circuits relative to GND	–0.5	1.32	V
MGTAVTTTX	Analog supply voltage for the GTP transmitter termination circuit relative to GND	–0.5	1.32	V
MGTAVTTRX	Analog supply voltage for the GTP receiver termination circuit relative to GND	–0.5	1.32	V
MGTAVCCPLL	Analog supply voltage for the GTP transmitter and receiver PLL circuits relative to GND	–0.5	1.32	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTP transceiver bank (top or bottom)	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.32	V
$V_{MGTREFCLK}$	Reference clock absolute input voltage	–0.5	1.32	V

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.

Table 13: **Recommended Operating Conditions for GTP Transceivers(1)(2)(3)**

Symbol	Description	Min	Typ	Max	Units
MGTAVCC	Analog supply voltage for the GTP transmitter and receiver circuits relative to GND	1.14	1.20	1.26	V
MGTAVTTTX	Analog supply voltage for the GTP transmitter termination circuit relative to GND	1.14	1.20	1.26	V
MGTAVTTRX	Analog supply voltage for the GTP receiver termination circuit relative to GND	1.14	1.20	1.26	V
MGTAVCCPLL	Analog supply voltage for the GTP transmitter and receiver PLL circuits relative to GND	1.14	1.20	1.26	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTP transceiver bank (top or bottom)	1.14	1.20	1.26	V

Notes:

1. Each voltage listed requires the filter circuit described in UG386: *Spartan-6 FPGA GTP Transceivers User Guide*.
2. Voltages are specified for the temperature range of T_j = –40°C to +125°C.
3. The voltage level of MGTAVCCPLL must not exceed the voltage level of MGTAVCC +10mV. The voltage level of MGTAVCC must not exceed the voltage level of MGTAVCCPLL.

Table 14: GTP Transceiver Current Supply (per Lane)

Symbol	Description	Typ(1)	Max	Units
$I_{MGTAVCC}$	GTP transceiver internal analog supply current	40.4	Note 2	mA
$I_{MGTAVTTTX}$	GTP transmitter termination supply current	27.4		mA
$I_{MGTAVTTRX}$	GTP receiver termination supply current	13.6		mA
$I_{MGTAVCCPLL}$	GTP transmitter and receiver PLL supply current	28.7		mA
$R_{MGTRREF}$	Precision reference resistor for internal calibration termination	50.0 ± 1% tolerance		Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C, with a 2.5 Gb/s line rate, with a shared PLL use mode.
2. Values for currents of other transceiver configurations and conditions can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.

Table 15: GTP Transceiver Quiescent Supply Current (per Lane)(1)(2)(3)(4)

Symbol	Description	Typ(5)	Max	Units
$I_{MGTAVCCQ}$	Quiescent MGTAVCC supply current	1.7	Note 2	mA
$I_{MGTAVTTTXQ}$	Quiescent MGTAVTTTX supply current	0.1		mA
$I_{MGTAVTTRXQ}$	Quiescent MGTAVTTRX supply current	1.2		mA
$I_{MGTAVCCPLLQ}$	Quiescent MGTAVCCPLL supply current	1.0		mA

Notes:

1. Device powered and unconfigured.
2. Currents for conditions other than values specified in this table can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.
3. GTP transceiver quiescent supply current for an entire device can be calculated by multiplying the values in this table by the number of available GTP transceivers.
4. Does not include power-up MGTAVTTRCAL supply current during device configuration.
5. Typical values are specified at nominal voltage, 25°C.

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	
LVTTL, QUIETIO, 2 mA	1.35	1.47	1.60	1.82	5.39	5.53	5.73	6.37	5.39	5.53	5.73	6.37	ns
LVTTL, QUIETIO, 4 mA	1.35	1.47	1.60	1.82	4.29	4.43	4.63	5.22	4.29	4.43	4.63	5.22	ns
LVTTL, QUIETIO, 6 mA	1.35	1.47	1.60	1.82	3.75	3.89	4.09	4.69	3.75	3.89	4.09	4.69	ns
LVTTL, QUIETIO, 8 mA	1.35	1.47	1.60	1.82	3.23	3.37	3.57	4.20	3.23	3.37	3.57	4.20	ns
LVTTL, QUIETIO, 12 mA	1.35	1.47	1.60	1.82	3.28	3.42	3.62	4.22	3.28	3.42	3.62	4.22	ns
LVTTL, QUIETIO, 16 mA	1.35	1.47	1.60	1.82	2.94	3.08	3.28	3.92	2.94	3.08	3.28	3.92	ns
LVTTL, QUIETIO, 24 mA	1.35	1.47	1.60	1.82	2.69	2.83	3.03	3.67	2.69	2.83	3.03	3.67	ns
LVTTL, Slow, 2 mA	1.35	1.47	1.60	1.82	4.36	4.50	4.70	5.30	4.36	4.50	4.70	5.30	ns
LVTTL, Slow, 4 mA	1.35	1.47	1.60	1.82	3.17	3.31	3.51	4.16	3.17	3.31	3.51	4.16	ns
LVTTL, Slow, 6 mA	1.35	1.47	1.60	1.82	2.76	2.90	3.10	3.75	2.76	2.90	3.10	3.75	ns
LVTTL, Slow, 8 mA	1.35	1.47	1.60	1.82	2.59	2.73	2.93	3.55	2.59	2.73	2.93	3.55	ns
LVTTL, Slow, 12 mA	1.35	1.47	1.60	1.82	2.58	2.72	2.92	3.54	2.58	2.72	2.92	3.54	ns
LVTTL, Slow, 16 mA	1.35	1.47	1.60	1.82	2.39	2.53	2.73	3.40	2.39	2.53	2.73	3.40	ns
LVTTL, Slow, 24 mA	1.35	1.47	1.60	1.82	2.28	2.42	2.62	3.24	2.28	2.42	2.62	3.24	ns
LVTTL, Fast, 2 mA	1.35	1.47	1.60	1.82	3.78	3.92	4.12	4.74	3.78	3.92	4.12	4.74	ns
LVTTL, Fast, 4 mA	1.35	1.47	1.60	1.82	2.49	2.63	2.83	3.45	2.49	2.63	2.83	3.45	ns
LVTTL, Fast, 6 mA	1.35	1.47	1.60	1.82	2.44	2.58	2.78	3.40	2.44	2.58	2.78	3.40	ns
LVTTL, Fast, 8 mA	1.35	1.47	1.60	1.82	2.32	2.46	2.66	3.28	2.32	2.46	2.66	3.28	ns
LVTTL, Fast, 12 mA	1.35	1.47	1.60	1.82	1.83	1.97	2.17	2.79	1.83	1.97	2.17	2.79	ns
LVTTL, Fast, 16 mA	1.35	1.47	1.60	1.82	1.83	1.97	2.17	2.79	1.83	1.97	2.17	2.79	ns
LVTTL, Fast, 24 mA	1.35	1.47	1.60	1.82	1.83	1.97	2.17	2.79	1.83	1.97	2.17	2.79	ns
LVCMOS33, QUIETIO, 2 mA	1.34	1.46	1.59	1.82	5.40	5.54	5.74	6.37	5.40	5.54	5.74	6.37	ns
LVCMOS33, QUIETIO, 4 mA	1.34	1.46	1.59	1.82	4.03	4.17	4.37	5.01	4.03	4.17	4.37	5.01	ns
LVCMOS33, QUIETIO, 6 mA	1.34	1.46	1.59	1.82	3.51	3.65	3.85	4.47	3.51	3.65	3.85	4.47	ns
LVCMOS33, QUIETIO, 8 mA	1.34	1.46	1.59	1.82	3.37	3.51	3.71	4.33	3.37	3.51	3.71	4.33	ns
LVCMOS33, QUIETIO, 12 mA	1.34	1.46	1.59	1.82	2.94	3.08	3.28	3.93	2.94	3.08	3.28	3.93	ns
LVCMOS33, QUIETIO, 16 mA	1.34	1.46	1.59	1.82	2.77	2.91	3.11	3.78	2.77	2.91	3.11	3.78	ns
LVCMOS33, QUIETIO, 24 mA	1.34	1.46	1.59	1.82	2.59	2.73	2.93	3.58	2.59	2.73	2.93	3.58	ns
LVCMOS33, Slow, 2 mA	1.34	1.46	1.59	1.82	4.37	4.51	4.71	5.28	4.37	4.51	4.71	5.28	ns
LVCMOS33, Slow, 4 mA	1.34	1.46	1.59	1.82	2.98	3.12	3.32	3.94	2.98	3.12	3.32	3.94	ns
LVCMOS33, Slow, 6 mA	1.34	1.46	1.59	1.82	2.58	2.72	2.92	3.61	2.58	2.72	2.92	3.61	ns
LVCMOS33, Slow, 8 mA	1.34	1.46	1.59	1.82	2.65	2.79	2.99	3.61	2.65	2.79	2.99	3.61	ns
LVCMOS33, Slow, 12 mA	1.34	1.46	1.59	1.82	2.39	2.53	2.73	3.31	2.39	2.53	2.73	3.31	ns
LVCMOS33, Slow, 16 mA	1.34	1.46	1.59	1.82	2.31	2.45	2.65	3.27	2.31	2.45	2.65	3.27	ns
LVCMOS33, Slow, 24 mA	1.34	1.46	1.59	1.82	2.28	2.42	2.62	3.24	2.28	2.42	2.62	3.24	ns
LVCMOS33, Fast, 2 mA	1.34	1.46	1.59	1.82	3.76	3.90	4.10	4.70	3.76	3.90	4.10	4.70	ns
LVCMOS33, Fast, 4 mA	1.34	1.46	1.59	1.82	2.48	2.62	2.82	3.44	2.48	2.62	2.82	3.44	ns
LVCMOS33, Fast, 6 mA	1.34	1.46	1.59	1.82	2.32	2.46	2.66	3.28	2.32	2.46	2.66	3.28	ns

Table 29: **IOB Switching Characteristics for the Automotive XA Spartan-6 and the Spartan-6Q Devices**(1) ***(Cont'd)***

I/O Standard	T_{IOPI}		T_{IOOP}		T_{IOTP}		Units
	Speed Grade		Speed Grade		Speed Grade		
	-3	-2	-3	-2	-3	-2	
LVCMOS18, QUIETIO, 16 mA	1.25	1.43	3.34	3.54	3.34	3.54	ns
LVCMOS18, QUIETIO, 24 mA	1.25	1.43	3.18	3.38	3.18	3.38	ns
LVCMOS18, Slow, 2 mA	1.25	1.43	4.79	4.99	4.79	4.99	ns
LVCMOS18, Slow, 4 mA	1.25	1.43	3.84	4.04	3.84	4.04	ns
LVCMOS18, Slow, 6 mA	1.25	1.43	3.17	3.37	3.17	3.37	ns
LVCMOS18, Slow, 8 mA	1.25	1.43	2.37	2.57	2.37	2.57	ns
LVCMOS18, Slow, 12 mA	1.25	1.43	2.13	2.33	2.13	2.33	ns
LVCMOS18, Slow, 16 mA	1.25	1.43	2.13	2.33	2.13	2.33	ns
LVCMOS18, Slow, 24 mA	1.25	1.43	2.13	2.33	2.13	2.33	ns
LVCMOS18, Fast, 2 mA	1.25	1.43	3.78	3.98	3.78	3.98	ns
LVCMOS18, Fast, 4 mA	1.25	1.43	2.54	2.74	2.54	2.74	ns
LVCMOS18, Fast, 6 mA	1.25	1.43	2.02	2.22	2.02	2.22	ns
LVCMOS18, Fast, 8 mA	1.25	1.43	1.95	2.15	1.95	2.15	ns
LVCMOS18, Fast, 12 mA	1.25	1.43	1.85	2.05	1.85	2.05	ns
LVCMOS18, Fast, 16 mA	1.25	1.43	1.85	2.05	1.85	2.05	ns
LVCMOS18, Fast, 24 mA	1.25	1.43	1.85	2.05	1.85	2.05	ns
LVCMOS18_JEDEC, QUIETIO, 2 mA	1.01	1.19	6.09	6.29	6.09	6.29	ns
LVCMOS18_JEDEC, QUIETIO, 4 mA	1.01	1.19	4.89	5.09	4.89	5.09	ns
LVCMOS18_JEDEC, QUIETIO, 6 mA	1.01	1.19	4.20	4.40	4.20	4.40	ns
LVCMOS18_JEDEC, QUIETIO, 8 mA	1.01	1.19	3.87	4.07	3.87	4.07	ns
LVCMOS18_JEDEC, QUIETIO, 12 mA	1.01	1.19	3.49	3.69	3.49	3.69	ns
LVCMOS18_JEDEC, QUIETIO, 16 mA	1.01	1.19	3.34	3.54	3.34	3.54	ns
LVCMOS18_JEDEC, QUIETIO, 24 mA	1.01	1.19	3.17	3.37	3.17	3.37	ns
LVCMOS18_JEDEC, Slow, 2 mA	1.01	1.19	4.79	4.99	4.79	4.99	ns
LVCMOS18_JEDEC, Slow, 4 mA	1.01	1.19	3.84	4.04	3.84	4.04	ns
LVCMOS18_JEDEC, Slow, 6 mA	1.01	1.19	3.18	3.38	3.18	3.38	ns
LVCMOS18_JEDEC, Slow, 8 mA	1.01	1.19	2.37	2.57	2.37	2.57	ns
LVCMOS18_JEDEC, Slow, 12 mA	1.01	1.19	2.13	2.33	2.13	2.33	ns
LVCMOS18_JEDEC, Slow, 16 mA	1.01	1.19	2.13	2.33	2.13	2.33	ns
LVCMOS18_JEDEC, Slow, 24 mA	1.01	1.19	2.13	2.33	2.13	2.33	ns
LVCMOS18_JEDEC, Fast, 2 mA	1.01	1.19	3.75	3.95	3.75	3.95	ns
LVCMOS18_JEDEC, Fast, 4 mA	1.01	1.19	2.54	2.74	2.54	2.74	ns
LVCMOS18_JEDEC, Fast, 6 mA	1.01	1.19	2.02	2.22	2.02	2.22	ns
LVCMOS18_JEDEC, Fast, 8 mA	1.01	1.19	1.94	2.14	1.94	2.14	ns
LVCMOS18_JEDEC, Fast, 12 mA	1.01	1.19	1.86	2.06	1.86	2.06	ns
LVCMOS18_JEDEC, Fast, 16 mA	1.01	1.19	1.86	2.06	1.86	2.06	ns
LVCMOS18_JEDEC, Fast, 24 mA	1.01	1.19	1.86	2.06	1.86	2.06	ns

Table 34: **SSO Limit per V_{CCO}/GND Pair** ***(Cont'd)***

V_{CCO}	I/O Standard	Drive	Slew	SSO Limit per V_{CCO}/GND Pair			
				All TQG144, CPG196, CSG225, FT(G)256, and LX devices in CSG324		All CS(G)484, FG(G)484, FG(G)676, FG(G)900, and LXT devices in CSG324	
				Bank 0/2	Bank 1/3	Bank 0/2	Bank 1/3/4/5
1.8V	LVCMOS18, LVCMOS18_JEDEC	2	Fast	39	46	39	47
			Slow	65	75	65	74
			QuietIO	80	80	80	85
		4	Fast	22	25	22	25
			Slow	38	36	38	29
			QuietIO	45	40	45	35
		6	Fast	16	18	16	17
			Slow	27	25	27	19
			QuietIO	30	28	30	23
		8	Fast	13	15	13	14
			Slow	16	18	16	16
			QuietIO	25	22	25	18
		12	Fast	5	7	5	5
			Slow	7	8	7	6
			QuietIO	11	10	11	8
		16	Fast	4	5	4	4
			Slow	7	8	7	5
			QuietIO	11	10	11	8
		24	Fast	N/A	5	N/A	3
			Slow	N/A	8	N/A	8
			QuietIO	N/A	10	N/A	8
	HSTL_I_18			9	10	9	9
	HSTL_II_18			N/A	5	N/A	6
	HSTL_III_18			9	10	9	11
	DIFF_HSTL_I_18			27	30	27	27
	DIFF_HSTL_II_18			N/A	15	N/A	18
	DIFF_HSTL_III_18			27	30	27	33
	MOBILE_DDR (3)			12	14	12	14
	DIFF_MOBILE_DDR (3)			36	42	36	42
	SSTL_18_I (3)			9	10	9	10
	SSTL_18_II (3)			N/A	5	N/A	4
	DIFF_SSTL_18_I (3)			27	30	27	30
	DIFF_SSTL_18_II (3)			N/A	15	N/A	12

Input/Output Delay Switching Characteristics

Table 39: **IODELAY2 Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L[3]	
T_{IODCCK_CAL} / T_{IODCKC_CAL}	CAL pin Setup/Hold with respect to CK	0.28/ –0.13	0.33/ –0.13	0.48/ –0.13	N/A	ns
T_{IODCCK_CE} / T_{IODCKC_CE}	CE pin Setup/Hold with respect to CK	0.17/ –0.03	0.17/ –0.03	0.25/ –0.02	N/A	ns
T_{IODCCK_INC}/ T_{IODCKC_INC}	INC pin Setup/Hold with respect to CK	0.10/ 0.02	0.12/ 0.03	0.18/ 0.06	N/A	ns
T_{IODCCK_RST}/ T_{IODCKC_RST}	RST pin Setup/Hold with respect to CK	0.12/ –0.02	0.15/ –0.02	0.22/ –0.01	N/A	ns
T_{TAP1}[2]	Maximum tap 1 delay	8	14	16	N/A	ps
T_{TAP2}	Maximum tap 2 delay	40	66	77	N/A	ps
T_{TAP3}	Maximum tap 3 delay	95	120	140	N/A	ps
T_{TAP4}	Maximum tap 4 delay	108	141	166	N/A	ps
T_{TAP5}	Maximum tap 5 delay	171	194	231	N/A	ps
T_{TAP6}	Maximum tap 6 delay	207	249	292	N/A	ps
T_{TAP7}	Maximum tap 7 delay	212	276	343	N/A	ps
T_{TAP8}	Maximum tap 8 delay	322	341	424	N/A	ps
F_{MINCAL}	Minimum allowed bit rate for calibration in variable mode: VARIABLE_FROM_ZERO, VARIABLE_FROM_HALF_MAX, and DIFF_PHASE_DETECTOR.	188	188	188	N/A	Mb/s
$T_{IODDO\_IDATAIN}$	Propagation delay through IODELAY2	Note 1	Note 1	Note 1	Note 3	–
$T_{IODDO\_ODATAIN}$	Propagation delay through IODELAY2	Note 1	Note 1	Note 1	Note 3	–

Notes:

1. Delay depends on IODELAY2 tap setting. See TRACE report for actual values.
2. Maximum delay = integer (number of taps/8) × T_{TAP8} + T_{TAPn} (where n equals the remainder). For minimum delay consult the TRACE setup and hold report. Minimum delay is typically greater than 30% of the maximum delay. Tap delays can vary by device and overall conditions. See TRACE report for actual values.
3. Spartan-6 -1L devices only support tap 0. See TRACE report for actual values.

Table 54: Switching Characteristics for the Delay-Locked Loop (DLL)[1] *(Cont'd)*

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
LOCK_DLL[3]	When using the DLL alone: The time from deassertion at the DCM's reset input to the rising transition at its LOCKED output. When the DCM is locked, the CLKIN and CLKFB signals are in phase. CLKIN_FREQ_DLL < 50 MHz.	–	5	–	5	–	5	–	5	ms
	When using the DLL alone: The time from deassertion at the DCM's reset input to the rising transition at its LOCKED output. When the DCM is locked, the CLKIN and CLKFB signals are in phase. CLKIN_FREQ_DLL > 50 MHz	–	0.60	–	0.60	–	0.60	–	0.60	ms
Delay Lines										
DCM_DELAY_STEP[5]	Finest delay resolution, averaged over all steps.	10	40	10	40	10	40	10	40	ps

Notes:

1. The values in this table are based on the operating conditions described in Table 2 and Table 53.
2. Indicates the maximum amount of output jitter that the DCM adds to the jitter on the CLKIN input.
3. For optimal jitter tolerance and faster LOCK time, use the CLKIN_PERIOD attribute.
4. Some jitter and duty-cycle specifications include 1% of input clock period or 0.01 UI. For example, this data sheet specifies a maximum jitter of ±(1% of CLKIN period + 150 ps). Assuming that the CLKIN frequency is 100 MHz, the equivalent CLKIN period is 10 ns. Since 1% of 10 ns is 0.1 ns or 100 ps, the maximum jitter is ±(100 ps + 150 ps) = ±250 ps.
5. A typical delay step size is 23 ps.
6. The timing analysis tools use the CLK_FEEDBACK = 1X condition for the CLKIN_CLKFB_PHASE value (reported as phase error). When using CLK_FEEDBACK = 2X, add 100 ps to the phase error for the CLKIN_CLKFB_PHASE value (as shown in this table).

Table 55: Recommended Operating Conditions for the Digital Frequency Synthesizer (DFS)[1]

Symbol	Description	Speed Grade								Units
		-3		-3N		-2		-1L		
		Min	Max	Min	Max	Min	Max	Min	Max	
Input Frequency Ranges[2]										
CLKIN_FREQ_FX	Frequency for the CLKIN input. Also described as F_{CLKIN}.	0.5	375[3]	0.5	375[3]	0.5	333[3]	0.5	200[3]	MHz
Input Clock Jitter Tolerance[4]										
CLKIN_CYC_JITT_FX_LF	Cycle-to-cycle jitter at the CLKIN input, based on CLKFX output frequency: FCLKFX < 150 MHz.	–	±300	–	±300	–	±300	–	±300	ps
CLKIN_CYC_JITT_FX_HF	Cycle-to-cycle jitter at the CLKIN input, based on CLKFX output frequency: FCLKFX > 150 MHz.	–	±150	–	±150	–	±150	–	±150	ps
CLKIN_PER_JITT_FX	Period jitter at the CLKIN input.	–	±1	–	±1	–	±1	–	±1	ns

Notes:

1. DFS specifications apply when using either of the DFS outputs (CLKFX or CLKFX180).
2. When using both DFS and DLL outputs on the same DCM, follow the more restrictive CLKIN_FREQ_DLL specifications in Table 53.
3. The CLKIN_DIVIDE_BY_2 attribute increases the effective input frequency range. When set to TRUE, the input clock frequency is divided by two as it enters the DCM. Input clock frequencies for the clock buffer being used can be increased up to the F_{MAX} (see Table 48 and Table 49 for BUFG and BUFIO2 limits).
4. CLKIN input jitter beyond these limits can cause the DCM to lose LOCK.

Table 59: Switching Characteristics for the Phase-Shift Clock in Variable Phase Mode(1)

Symbol	Description	Amount of Phase Shift	Units
Phase Shifting Range			
MAX_STEPS(2)	When CLKIN < 60 MHz, the maximum allowed number of DCM_DELAY_STEP steps for a given CLKIN clock period, where T = CLKIN clock period in ns. When using CLKIN_DIVIDE_BY_2 = TRUE, double the clock-effective clock period.	±(INTEGER(10 x (TCLKIN – 3 ns)))	steps
	When CLKIN ≥ 60 MHz, the maximum allowed number of DCM_DELAY_STEP steps for a given CLKIN clock period, where T = CLKIN clock period in ns. When using CLKIN_DIVIDE_BY_2 = TRUE, double the clock-effective clock period.	±(INTEGER(15 x (TCLKIN – 3 ns)))	steps
FINE_SHIFT_RANGE_MIN	Minimum guaranteed delay for variable phase shifting.	±(MAX_STEPS x DCM_DELAY_STEP_MIN)	ps
FINE_SHIFT_RANGE_MAX	Maximum guaranteed delay for variable phase shifting	±(MAX_STEPS x DCM_DELAY_STEP_MAX)	ps

Notes:

1. The values in this table are based on the operating conditions described in Table 53 and Table 58.
2. The maximum variable phase shift range, MAX_STEPS, is only valid when the DCM has no initial fixed-phase shifting, that is, the PHASE_SHIFT attribute is set to 0.
3. The DCM_DELAY_STEP values are provided at the end of Table 54.

Table 60: Miscellaneous DCM Timing Parameters(1)

Symbol	Description	Min	Max	Units
DCM_RST_PW_MIN	Minimum duration of a RST pulse width	3	–	CLKIN cycles

Notes:

1. This limit only applies to applications that use the DCM DLL outputs (CLK0, CLK90, CLK180, CLK270, CLK2X, CLK2X180, and CLKDV). The DCM DFS outputs (CLKFX, CLKFXDV, CLKFX180) are unaffected.

Table 61: Frequency Synthesis

Attribute	Min	Max
CLKFX_MULTIPLY (DCM_SP)	2	32
CLKFX_DIVIDE (DCM_SP)	1	32
CLKDV_DIVIDE (DCM_SP)	1.5	16
CLKFX_MULTIPLY (DCM_CLKGEN)	2	256
CLKFX_DIVIDE (DCM_CLKGEN)	1	256
CLKFXDV_DIVIDE (DCM_CLKGEN)	2	32

Table 62: DCM Switching Characteristics

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
T_{DMCCK_PSEN}/ T_{DMCKC_PSEN}	PSEN Setup/Hold	1.50/ 0.00	1.50/ 0.00	1.50/ 0.00	1.50/ 0.00	ns
$T_{DMCCK\_PSINCDEC}$/ $T_{DMCKC\_PSINCDEC}$	PSINCDEC Setup/Hold	1.50/ 0.00	1.50/ 0.00	1.50/ 0.00	1.50/ 0.00	ns
T_{DMCKO_PSDONE}	Clock to out of PSDONE	1.50	1.50	1.50	1.50	ns

Table 65: **Global Clock Input to Output Delay With DCM in Source-Synchronous Mode**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
LVCMOS25 Global Clock Input to Output Delay using Output Flip-Flop, 12mA, Fast Slew Rate, *with* DCM in Source-Synchronous Mode.							
$T_{ICKOFDCM\_0}$	Global Clock and OUTFF *with* DCM	XC6SLX4	5.03	N/A	7.21	8.05	ns
		XC6SLX9	5.03	6.13	7.21	8.05	ns
		XC6SLX16	5.08	5.51	6.44	7.96	ns
		XC6SLX25	4.81	5.13	5.69	7.94	ns
		XC6SLX25T	4.81	5.13	5.69	N/A	ns
		XC6SLX45	5.26	5.69	6.63	7.92	ns
		XC6SLX45T	5.26	5.69	6.63	N/A	ns
		XC6SLX75	4.77	5.18	5.88	7.95	ns
		XC6SLX75T	4.77	5.18	5.88	N/A	ns
		XC6SLX100	4.72	5.11	5.76	8.59	ns
		XC6SLX100T	4.76	5.11	5.76	N/A	ns
		XC6SLX150	4.90	5.30	5.93	7.93	ns
		XC6SLX150T	4.90	5.30	5.93	N/A	ns
		XA6SLX4	5.35	N/A	7.21	N/A	ns
		XA6SLX9	5.35	N/A	7.21	N/A	ns
		XA6SLX16	5.42	N/A	6.44	N/A	ns
		XA6SLX25	5.13	N/A	5.69	N/A	ns
		XA6SLX25T	5.13	N/A	5.79	N/A	ns
		XA6SLX45	5.58	N/A	6.63	N/A	ns
		XA6SLX45T	5.58	N/A	6.63	N/A	ns
		XA6SLX75	5.09	N/A	5.87	N/A	ns
		XA6SLX75T	5.09	N/A	5.87	N/A	ns
		XA6SLX100	N/A	N/A	6.44	N/A	ns
		XQ6SLX75	N/A	N/A	5.87	7.95	ns
		XQ6SLX75T	5.09	N/A	5.87	N/A	ns
		XQ6SLX150	N/A	N/A	6.06	7.93	ns
		XQ6SLX150T	5.50	N/A	6.06	N/A	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. DCM output jitter is already included in the timing calculation.

Table 73: **Global Clock Setup and Hold With DCM in Source-Synchronous Mode**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for LVCMOS25 Standard.[1]							
T_{PSDCM0}/ T_{PHDCM0}	No Delay Global Clock and IFF[2] with DCM in Source-Synchronous Mode	XC6SLX4	0.71/0.65	N/A	0.72/1.22	1.58/1.18	ns
		XC6SLX9	0.71/0.69	0.71/1.19	0.72/1.36	1.58/1.18	ns
		XC6SLX16	0.86/0.52	0.92/0.57	1.04/0.60	1.02/1.06	ns
		XC6SLX25	0.84/0.58	0.90/0.59	1.01/0.59	1.58/1.07	ns
		XC6SLX25T	0.84/0.58	0.90/0.59	1.01/0.59	N/A	ns
		XC6SLX45	0.85/0.70	0.90/0.76	0.98/0.79	1.34/1.34	ns
		XC6SLX45T	0.85/0.70	0.90/0.76	0.98/0.79	N/A	ns
		XC6SLX75	1.00/0.62	1.06/0.63	1.15/0.63	1.65/1.46	ns
		XC6SLX75T	1.00/0.71	1.06/0.72	1.15/0.72	N/A	ns
		XC6SLX100	0.81/0.68	0.81/0.69	0.94/0.69	1.42/2.07	ns
		XC6SLX100T	0.81/0.68	0.81/0.69	0.94/0.69	N/A	ns
		XC6SLX150	0.68/0.98	0.69/0.99	0.79/0.99	1.45/1.60	ns
		XC6SLX150T	0.68/0.98	0.69/0.99	0.79/0.99	N/A	ns
		XA6SLX4	0.81/0.74	N/A	0.72/1.36	N/A	ns
		XA6SLX9	0.81/0.74	N/A	0.72/1.36	N/A	ns
		XA6SLX16	1.01/0.56	N/A	1.04/0.60	N/A	ns
		XA6SLX25	0.94/0.76	N/A	1.06/0.77	N/A	ns
		XA6SLX25T	0.94/0.76	N/A	1.14/0.77	N/A	ns
		XA6SLX45	0.86/0.74	N/A	0.98/0.78	N/A	ns
		XA6SLX45T	0.86/0.74	N/A	0.98/0.78	N/A	ns
		XA6SLX75	1.02/0.71	N/A	1.15/0.72	N/A	ns
		XA6SLX75T	1.02/0.71	N/A	1.15/0.72	N/A	ns
		XA6SLX100	N/A	N/A	1.37/0.75	N/A	ns
		XQ6SLX75	N/A	N/A	1.15/0.72	1.65/1.46	ns
		XQ6SLX75T	1.02/0.71	N/A	1.15/0.72	N/A	ns
		XQ6SLX150	N/A	N/A	0.79/1.15	1.45/1.60	ns
		XQ6SLX150T	0.73/1.15	N/A	0.79/1.15	N/A	ns

Notes:

1. Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage. These measurements include DCM CLK0 jitter.
2. IFF = Input Flip-Flop or Latch
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 75: **Global Clock Setup and Hold With PLL in Source-Synchronous Mode**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for LVCMOS25 Standard.[1]							
T_{PSPLL0}/ T_{PHPLL0}	No Delay Global Clock and IFF[2] with PLL in Source-Synchronous Mode	XC6SLX4	0.47/1.08	N/A	0.47/1.60	1.15/1.68	ns
		XC6SLX9	0.47/1.08	0.47/1.35	0.47/1.60	1.15/1.68	ns
		XC6SLX16	0.37/0.75	0.37/0.82	0.51/0.94	0.57/1.31	ns
		XC6SLX25	0.69/1.06	0.69/1.06	0.69/1.06	1.86/1.67	ns
		XC6SLX25T	0.69/1.06	0.69/1.06	0.69/1.06	N/A	ns
		XC6SLX45	0.57/1.05	0.65/1.10	0.65/1.18	1.02/1.65	ns
		XC6SLX45T	0.57/1.06	0.65/1.10	0.65/1.18	N/A	ns
		XC6SLX75	0.86/1.04	0.87/1.04	0.90/1.04	1.34/1.55	ns
		XC6SLX75T	0.86/1.04	0.87/1.04	0.90/1.04	N/A	ns
		XC6SLX100	0.53/1.13	0.54/1.13	0.55/1.13	0.89/2.39	ns
		XC6SLX100T	0.53/1.13	0.54/1.13	0.55/1.13	N/A	ns
		XC6SLX150	0.50/1.31	0.51/1.31	0.52/1.31	1.02/1.72	ns
		XC6SLX150T	0.50/1.31	0.51/1.31	0.52/1.31	N/A	ns
		XA6SLX4	0.71/0.93	N/A	0.62/1.47	N/A	ns
		XA6SLX9	0.71/0.93	N/A	0.62/1.47	N/A	ns
		XA6SLX16	0.92/0.69	N/A	0.63/0.82	N/A	ns
		XA6SLX25	0.99/0.94	N/A	0.96/0.94	N/A	ns
		XA6SLX25T	0.99/0.94	N/A	1.04/0.94	N/A	ns
		XA6SLX45	0.63/1.02	N/A	0.72/1.05	N/A	ns
		XA6SLX45T	0.63/1.02	N/A	0.72/1.05	N/A	ns
		XA6SLX75	0.88/0.89	N/A	1.02/0.89	N/A	ns
		XA6SLX75T	0.88/0.89	N/A	1.02/0.89	N/A	ns
		XA6SLX100	N/A	N/A	1.25/0.96	N/A	ns
		XQ6SLX75	N/A	N/A	1.02/0.89	1.34/1.55	ns
		XQ6SLX75T	0.88/0.89	N/A	1.02/0.89	N/A	ns
		XQ6SLX150	N/A	N/A	0.63/1.19	1.02/1.72	ns
		XQ6SLX150T	0.60/1.19	N/A	0.63/1.19	N/A	ns

Notes:

1. Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage. These measurements include PLL CLKOUT0 jitter.
2. IFF = Input Flip-Flop or Latch
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 77: **Global Clock Setup and Hold With DCM and PLL in Source-Synchronous Mode**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
Example Data Input Set-Up and Hold Times Relative to a Forwarded Clock Input Pin,(1) Using DCM, PLL, and Global Clock Buffer for the LVCMOS25 standard.							
$T_{PSDCMPLL\_0}$/ $T_{PHDCMPLL\_0}$	No Delay Global Clock and IFF(2) with DCM in Source-Synchronous Mode and PLL in DCM2PLL Mode.	XC6SLX4	0.43/1.07	N/A	0.43/1.43	1.10/1.67	ns
		XC6SLX9	0.43/1.03	0.45/1.14	0.45/1.43	1.10/1.67	ns
		XC6SLX16	0.74/0.93	0.74/1.12	0.74/1.21	0.77/1.35	ns
		XC6SLX25	0.67/1.02	0.76/1.11	0.84/1.18	1.23/1.46	ns
		XC6SLX25T	0.67/1.02	0.76/1.11	0.84/1.18	N/A	ns
		XC6SLX45	0.65/0.99	0.65/1.04	0.71/1.12	1.18/1.58	ns
		XC6SLX45T	0.65/1.00	0.65/1.04	0.71/1.12	N/A	ns
		XC6SLX75	0.86/1.01	0.88/1.06	0.94/1.14	1.29/1.67	ns
		XC6SLX75T	0.86/1.01	0.88/1.06	0.94/1.14	N/A	ns
		XC6SLX100	0.50/1.10	0.56/1.10	0.61/1.17	0.84/2.24	ns
		XC6SLX100T	0.50/1.10	0.56/1.10	0.61/1.17	N/A	ns
		XC6SLX150	0.45/1.28	0.47/1.28	0.52/1.28	1.27/1.56	ns
		XC6SLX150T	0.45/1.28	0.47/1.28	0.52/1.28	N/A	ns
		XA6SLX4	0.74/1.00	N/A	0.74/1.43	N/A	ns
		XA6SLX9	0.74/1.00	N/A	0.74/1.43	N/A	ns
		XA6SLX16	1.81/1.15	N/A	1.81/1.03	N/A	ns
		XA6SLX25	0.89/1.01	N/A	0.96/1.05	N/A	ns
		XA6SLX25T	0.89/1.01	N/A	1.04/1.15	N/A	ns
		XA6SLX45	0.69/0.95	N/A	0.83/0.96	N/A	ns
		XA6SLX45T	0.69/0.95	N/A	0.83/0.96	N/A	ns
		XA6SLX75	0.88/0.94	N/A	1.06/0.96	N/A	ns
		XA6SLX75T	0.88/0.94	N/A	1.06/0.96	N/A	ns
		XA6SLX100	N/A	N/A	1.55/1.33	N/A	ns
		XQ6SLX75	N/A	N/A	1.06/0.96	1.29/1.67	ns
		XQ6SLX75T	0.88/0.94	N/A	1.06/0.96	N/A	ns
		XQ6SLX150	N/A	N/A	0.64/1.30	1.27/1.56	ns
		XQ6SLX150T	0.58/1.30	N/A	0.64/1.30	N/A	ns

Notes:

1. Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage. The timing values were measured using the fine-phase adjustment feature of the DCM. These measurements include CMT jitter; DCM CLK0 driving PLL, PLL CLKOUT0 driving BUFG. Package skew is not included in these measurements.
2. IFF = Input Flip-Flop

Revision History

The following table shows the revision history for this document.

Date	Version	Description of Revisions
06/24/09	1.0	Initial Xilinx release.
08/26/09	1.1	Added V_{FS} to Table 1and Table 2. Added R_{FUSE} to Table 2. Added XC6SLX75 and XC6SLX75T to V_{BATT} and I_{BATT} in Table 1, Table 2, and Table 4. Corrected the quiescent supply current for the XC6SLX4 in Table 5. Updated Table 11. Removed DV_{PPIN} from Figure 2. Removed $F_{PCIECORE}$ from Table 24 and added values to $F_{PCIEUSER}$. Added more networking applications to Table 25. Updated values for $T_{SUSPENDLOW\_AWAKE}$, $T_{SUSPEND\_ENABLE}$, and T_{SCP_AWAKE} in Table 46. Numerous changes to Table 47, page 54 including the addition of new values to various specifications, revising the $T_{SMCKCSO}$ description, and changing the units of T_{POR}. Also, removed *Dynamic Reconfiguration Port (DRP) for DCM and PLL Before and After DCLK section* from Table 47 and updated all the notes. In Table 52, added to F_{INMAX}, revised F_{OUTMAX}, and removed PLL Maximum Output Frequency for BUFIO2. Revised values for DCM_DELAY_STEP in Table 54. Updated CLKIN_FREQ_FX values in Table 55.
01/04/10	1.2	Added -4 speed grade to entire document. Updated speed specification of -4, -3, -2 speed grades to version 1.03. Added -1L speed grade numbers per speed specification 1.00. Updated T_{SOL} in Table 1. Added -1L rows for LVCMOS12, LVCMOS15, and LVCMOS18 in Table 9. Revised much of the detail in GTP Transceiver Specifications in Table 12 through Table 23. Added -2 data to Table 25. Updated F_{MAX} in Table 44. Updated descriptions for $T_{DNACLKL}$ and $T_{DNACLKH}$ in Table 45 and revised values for all parameters. Removed $T_{INITADDR}$ from Table 47 and added new data. Updated values in Table 48 through Table 62. Added Table 51 (BUFPLL) and Table 57 (DCM_CLKGEN). Removed $T_{LOCKMAX}$ note from Table 52. Updated note 3 in Table 53. In Table 79: removed XC6SLX75CSG324 and XC6SLX75TCSG324; added XC6SLX75FG(G)484 and XC6SLX75FG(G)484.
02/22/10	1.3	Production release of XC6SLX16 -2 speed grade devices. The changes to Table 26 and Table 27 includes updating this data sheet to the data in ISE v11.5 software with speed specification v1.06. Updated maximum of V_{IN} and V_{TS} and note 2 in Table 1. In Table 2, changed V_{IN}, added I_{IN} and note 5, revised notes 1, 6, and 7, and added note 8 to R_{FUSE}. In Table 4, removed previous note 1 and added data to I_{RPU}, I_{RPD}, and I_{BATT}, changed C_{IN}, added R_{DT} and R_{IN_TERM}, and added note 2 and 3. Updated V_{CCO2} in Table 6. Added Table 7 and Table 8. Removed PCI66_3 from Table 9. Updated PCI33_3 and I2C in Table 9. Updated the description of Table 11. Completely updated Table 25. Updated Table 28 including adding values for PCI33_3. Updated V_{REF} value for HSTL_III_18 in Table 31. Updates missing V_{REF} values in Table 32. Added Simultaneously Switching Outputs, page 36. Removed T_{GSRQ} and T_{RPW} from Table 35 and Table 36. Also removed T_{DOQ} from Table 36. Removed T_{ISDO_DO} and note 1 from Table 37. Removed T_{OSCCK_S} and combinatorial section from Table 38. In Table 39, removed T_{IODDO_T} and added new tap parameters and note 2. In Table 40, Table 41, and Table 42, made typographical edits and removed notes. Removed clock CLK section in Table 41. Removed clock CLK section and T_{REG_MUX} and T_{REG_M31} in Table 42. Added block RAM F_{MAX} values to Table 43. Updated values and added note 2 to Table 45. Added values to Table 46 and removed note 1. Numerous changes to Table 47. Completely updated Table 57. Revised data in Table 62. Removed note 3 from Table 71. Added values to Table 79. Added data to Table 80 and Table 81.
03/10/10	1.4	Production release of XC6SLX45 -2 speed grade devices, which includes changes to Table 26 and Table 27 updating this data sheet to the data in ISE v11.5 software with speed specification v1.07. Fixed R_{IN_TERM} description in Table 4. Added PCI66_3 to Table 7 and replaced note 1. Corrected note 1 and the V, Max for TMDS_33 in Table 8. In Table 10, added note 1 to LVPECL_33 and TMDS_33. Also updated specifications for TMDS_33. Updated the GTP Transceiver Specifications section including adding values to Table 16, Table 17, and Table 20 through Table 23. Added PCI66_3 back into Table 9, Table 28, Table 31, Table 32, and Table 34. Updated note 3 on Table 32. In Table 34, corrected some typographical errors and fixed SSO limits for bank1/3 in FG(G)484 package. Corrected T_{OSCKC_OCE} in Table 38. In Table 57, updated CLKFX_FREEZE_VAR and CLKFX_FREEZE_TEMP_SLOPE and added typical values to $T_{CENTER\_LOW\_SPREAD}$ and $T_{CENTER\_HIGH\_SPREAD}$. Updated and added values to Table 63 through Table 78, and Table 81. In Table 79, revised the XC6SLX16-CSG324 and the XC6SLX45-CSG484 and FG(G)484 values.

Date	Version	Description of Revisions
06/14/10	1.5	In Table 2, added note 5 and added temperature range to V_{FS} and R_{FUSE}. Removed speed grade delineation, revised I_{RPD} description, and updated note 2 in Table 4. Added note 2 to Table 7. Added DIFF_MOBILE_DDR to Table 8 and Table 10. Added note 4 to Table 15. Changed minimum DV_{PPIN} in Table 16. Updated $F_{GTPDRPCLK}$ in Table 19. Increased maximum T_{LLSKEW} in Table 22. Updated descriptions and added data to Table 23. Removed note 1 and added new data to the Networking Applications section in Table 25. Updated Table 26 and Table 27 to the data in ISE v12.1 software with speed specification v1.08. In Table 28, added DIFF_MOBILE_DDR and updated -4 speed grade data. Updated the maximum I/O pairs per bank in Table 33. Updated note 2 on Table 39. Revised the F_{MAX} in Table 44. In Table 47, updated description for $T_{SMCKCSO}$, revised values for T_{POR} and added Min value, added $T_{BPIICCK}$ and $T_{SPIICCK}$. Also in Table 47, added device dependencies to F_{SMCCK} and F_{RBCCK}. Updated and added data to Table 63 through Table 78, and Table 81. In Table 79, added data on the XC6SLX45-FG(G)676 and revised the XC6SLX45T and XC6SLX150T values. The following changes to this specification are addressed in the product change notice XCN10024, *MCB Performance and JTAG Revision Code for Spartan-6 LX16 and LX45 FPGAs*. In Table 2, revised the V_{CCINT} to add the memory controller block extended performance specifications. In Table 25, changed the standard specifications and added extended performance specifications for the memory controller block and note 2. Added note 4 and updated values in Table 34.
06/24/10	1.6	Production release of XC6SLX45T (-2 and -3 speed grades), XC6SLX16 and XC6SLX45 (-3 speed grade) devices which includes changes to Table 26 and Table 27 (ISE v12.1 software with speed specification v1.08). Added the -3N speed grade, which designates Spartan-6 devices that do not support MCB functionality. This includes changes to Table 2 (note 2), Table 25 (note 4), and Switching Characteristics (Table 26). Updated Simultaneously Switching Outputs discussion. Added -3 speed grade values for T_{TAP} and F_{MINCAL} values in Table 39. In Table 40, updated T_{RPW} (-2 and -3 speed grade) values and F_{TOG} (-3 speed grade) values. In Table 48, updated T_{GIO} (-2 and -3 speed grade) values. Updated -3 values in spread spectrum section of Table 57.
07/16/10	1.7	Production release of specific devices listed in Table 26 and Table 27 using ISE v12.2 software with speed specification v1.11. Added note 4 advising designers of the patch which contains v1.11. Also updated the -1L speed specification to v1.04. Updated numerous -4 and -1L values. Added -4 T_{TAP} values and F_{MINCAL} to Table 39. Revised T_{CINCK}/T_{CKCIN} in Table 40. In Table 41, revised T_{SHCKO}. In Table 42, revised T_{REG}. Added new -1L values to Table 47. Added and updated values in Table 79.
07/26/10	1.8	Production release of XC6SLX25, XC6SLX25T, XC6SLX100 and XC6SLX100T in the specific speed grades listed in Table 26 and Table 27 using ISE v12.2 software with speed specification v1.11. Added note 7 to Table 2 and moved V_{FS} and R_{FUSE} to a new Table 3. Added I_{HS} and note 4 to Table 4. Added note 1 to Table 28. Added and updated SSO limits per V_{CCO}/GND pairs in Table 34. Added note 3 to Table 47. In Table 54, removed -1L specifications for CLKOUT_PER_JITT_DV1/2 and revised CLKIN_CLKFB_PHASE and CLKOUT_PHASE_DLL values. Updated note 3 in both Table 56 and Table 57.
08/23/10	1.9	Updated values for $F_{GTPRANGE1}$, $F_{GTPRANGE2}$, and $F_{GPLLMIN}$ in Table 18. Revised -3 and -4 values in Table 21. Removed the -1L speed grade readback support restriction and note 3 in Table 47.
11/05/10	1.10	Production release of XC6SLX4 and XC6SLX9 in the specific speed grades listed in Table 26 and Table 27 using ISE v12.3 software with speed specification v1.12 for the -2 speed grade available in the 12.3 *Speed Files Patch*. Added note 3 advising designers of the patch which contains v1.12. In Table 2, added note 4. In Table 4, added note 2. In Table 10, added notes 2 and 3. In Table 44, added note 2. In Table 47, updated symbol for T_{SMWCCK}/T_{SMCCKW}, changed -1L values for $T_{USERCCLKH}$ and $T_{USERCCLKL}$, and added and revised the modes for F_{MCCK} and F_{SMCCK}. In Table 53, redefined and expanded description for CLKIN_FREQ_DLL and rewrote note 3. Updated title of Table 58. Also in Table 78, revised T_{DCD_CLK} for XC6SLX150 and XC6SLX150T. Changed description of T_{PSFD}/T_{PHFD} in Table 71. For the -1L speed grade, updated data sheet to ISE 12.3 software with speed specification v1.05 which revised the values in the following tables: Table 25, Table 28, Table 35, Table 36, Table 37, Table 40 through Table 43, Table 48 through Table 56, Table 62 through Table 78, Table 80, and Table 81. Updated Notice of Disclaimer.

Date	Version	Description of Revisions
09/14/11	2.4	Production release of the XA6SLX4 and XA6SLX9 devices in Table 26 and Table 27 using ISE v13.2 software with -2 and -3 speed specification v1.19. Added production released version of the XA6SLX100 to Table 26 and Table 27 using ISE v13.3 software with -2 speed specification v1.20. Updated R_{OUT_TERM} description in Table 4. Fixed the LVPECL V_H error in Table 31. Updated introduction in Simultaneously Switching Outputs. Added the XA6SLX100 to Table 63 through Table 78, and Table 81. Added Note 4 to Table 78 because the T_{CKSKEW} for the XC6SLX100 is not the same as the T_{CKSKEW} for the XA6SLX100. Revised the revision history for version 1.6 dated 06/24/10. Removed the parenthetical statement about the -3N speed grade: (specifications are identical to the -3 speed grade).
10/17/11	3.0	Changed the data sheet from Preliminary Product Specification to Product Specification. Updated the Switching Characteristics, page 19 speed specification version ISE v13.3 software to -2 and -3 speed specification v1.20 and -1L speed specification of v1.08. Also updated Note 1 in Table 27. In Table 43, *Block RAM Switching Characteristics*, the F_{MAX} value for the -2 speed grade has been changed from 260 MHz to 280 MHz. In Table 54, *Switching Characteristics for the DLL*, a Note 6 was added and linked to CLKIN_CLKFB_PHASE.